

Jerry M Woodall

List of Publications by Year in descending order

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30
papers

679
citations

758635

12
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31
all docs

31
docs citations

31
times ranked

591
citing authors

#	ARTICLE	IF	CITATIONS
1	Study on the liquid phase-derived activation mechanism in Al-rich alloy hydrolysis reaction for hydrogen production. <i>Energy</i> , 2022, 247, 123489.	4.5	12
2	Gallium Phosphide Solar Cell Structures with Improved Quantum Efficiencies. <i>Journal of Electronic Materials</i> , 2020, 49, 3435-3440.	1.0	4
3	Gallium oxide nanowires for UV detection with enhanced growth and material properties. <i>Scientific Reports</i> , 2020, 10, 21434.	1.6	22
4	Interface studies of molecular beam epitaxy (MBE) grown ZnSe/GaAs heterovalent structures. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	3
5	In situ grown single crystal aluminum as a nonalloyed ohmic contact to n-ZnSe by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 042204.	0.6	0
6	Strategies for improving flow rate control of hydrogen generated by Al-rich alloys for on-board applications. <i>International Journal of Hydrogen Energy</i> , 2019, 44, 27695-27703.	3.8	14
7	Solar Blind Photodetectors Enabled by Nanotextured In^{2+} -Ga ₂ O ₃ Films Grown via Oxidation of GaAs Substrates. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	1.0	42
8	Spontaneous delamination via compressive buckling facilitates large-scale In^{2+} -Ga ₂ O ₃ thin film transfer from reusable GaAs substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700102.	0.8	3
9	Growth and Characterization of Single Crystalline InN Grown on GaN by RF Sputtering for Robust Schottky Contacts. <i>Journal of Electronic Materials</i> , 2016, 45, 6305-6309.	1.0	0
10	Improved High-Energy Response of AlGaAs/GaAs Solar Cells Using a Low-Cost Technology. <i>Journal of Electronic Materials</i> , 2016, 45, 6317-6322.	1.0	1
11	Pulse laser deposition fabricated InP/Al-ZnO heterojunction solar cells with efficiency enhanced by an i-ZnO interlayer. <i>Applied Physics A: Materials Science and Processing</i> , 2015, 121, 1219-1226.	1.1	6
12	Layered Growth of Lattice-Mismatched Ga _x In _{1-x} P on GaP Substrates by Liquid Phase Epitaxy. <i>Journal of Electronic Materials</i> , 2014, 43, 894-901.	1.0	3
13	Hall Effect Studies of AlGaAs Grown by Liquid-Phase Epitaxy for Tandem Solar Cell Applications. <i>Journal of Electronic Materials</i> , 2014, 43, 3999-4002.	1.0	5
14	Photoluminescence Excitation Spectroscopy for In-Line Optical Characterization of Crystalline Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2013, 3, 1342-1347.	1.5	15
15	Design and modeling of a high efficiency hybrid photovoltaic-photothermal concentrator (PVPTC) system. , 2013, , .		1
16	Liquid phase-enabled reaction of Al-Ga and Al-Ga-In-Sn alloys with water. <i>International Journal of Hydrogen Energy</i> , 2011, 36, 5271-5279.	3.8	190
17	Design Guidelines for True Green LEDs and High Efficiency Photovoltaics Using ZnSe/GaAs Digital Alloys. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H5.	2.2	6
18	Drift dominated InP/GaP photodiodes. <i>Solid-State Electronics</i> , 2004, 48, 1975-1979.	0.8	1

#	ARTICLE	IF	CITATIONS
19	Gallium arsenide deep-level optical emitter for fibre optics. <i>Nature Materials</i> , 2003, 2, 375-378.	13.3	27
20	Intensity and spatial modulation of spontaneous emission in GaAs by field aperture selecting transport. <i>Applied Physics Letters</i> , 2003, 82, 3197-3199.	1.5	8
21	Electrical characteristics and thermal stability of W, WSiN, and Nb contacts to p- and n-type GaN. <i>Journal of Electronic Materials</i> , 1999, 28, 228-233.	1.0	10
22	Subpicosecond photoconductivity of In _{0.53} Ga _{0.47} As: Intervalley scattering rates observed via THz spectroscopy. <i>Physical Review B</i> , 1996, 54, 5568-5573.	1.1	41
23	Hole dominated transport in InGaAs metal semiconductor metal photodetectors. <i>Applied Physics Letters</i> , 1995, 67, 413-415.	1.5	3
24	Temperature Dependence of Quantized States in Strained-Layer In _{0.21} Ga _{0.79} As/GaAs Single Quantum Well. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 966-970.	0.8	23
25	Experimental comparison of strained quantum-wire and quantum-well laser characteristics. <i>Applied Physics Letters</i> , 1994, 64, 2211-2213.	1.5	21
26	Photoconductively switched antennas for measuring target resonances. <i>Applied Physics Letters</i> , 1994, 64, 2178-2180.	1.5	11
27	High efficiency and low threshold current strained V-groove quantum-wire lasers. <i>Applied Physics Letters</i> , 1994, 64, 3536-3538.	1.5	103
28	Solubility-limit activation of Si doping at MBE GaAs pn junctions observed by cross-sectional scanning tunneling microscopy. <i>Journal of Crystal Growth</i> , 1993, 127, 1030-1031.	0.7	0
29	Optical emission properties of semi-insulating GaAs grown at low temperatures by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992, 60, 3007-3009.	1.5	32
30	Photoelectrolysis of Water with Semiconductor Materials. <i>Journal of the Electrochemical Society</i> , 1977, 124, 1436-1440.	1.3	72